

INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

IRFS38N20D

D(2)

5(3)

pin 1, Oate

3

1 2

2, Drain

3, Source

FEATURES

- With To-262 package
- · Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Switching applications

| • ABSO | LUTE MAXIMUM RATINGS(Ta=25°C | TO-262 package | | | |
|------------------|---|---|------|---|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | |
| V _{DSS} | Drain-Source Voltage | 200 | V | | |
| V _{GSS} | Gate-Source Voltage | ±30 | V | | |
| ID | Drain Current-ContinuousTc=25°C Tc=100°C | 43 30 | A | | |
| I _{DM} | Drain Current-Single Pulsed | 180 | A | | |
| P _D | Total Dissipation @T _c =25℃ | 300 | w | - DIM MIN MAX <u>A</u> 4.37 4.77 <u>A1</u> 1.22 1.42 <u>A2</u> 2.47 2.87 | |
| T_{ch} | Max. Operating Junction Temperature | 175 | °C | b 0.70 0.97 b2 1.17 1.42 c 0.28 0.53 D 23.20 24.02 | |
| T _{stg} | Storage Temperature | -55~175 | °C | D1 8.38 8.90 D2 6.00 E 9.90 10.39 | |
| • THERM | MAL CHARACTERISTICS | - <u>E4</u> 7.30 - e 2.54BSC G 1.25 1.50 H2 - 1.31 | | | |
| SYMBOL | PARAMETER | МАХ | UNIT | L 13.34 14.10 L1 3.30 4.06 L3 0.95 1.15 | |

0.47

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Channel-to-case thermal resistance

Rth(ch-c)

°C/W



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | МАХ | UNIT |
|----------------------|--------------------------------|---|-----|-----|-----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =0.25mA | 200 | | | v |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} =V _{GS} ; I _D =0.25mA | 3.0 | | 5.0 | v |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =26A | | | 54 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±30V;V _{DS} =0V | | | ±0.1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =200V; V _{GS} = 0V;Tj=25℃ V _{DS} =160V; V _{GS} = 0V;Tj=125℃ | | | 25 250 | μA |
| V _{SDF} | Diode forward voltage | I _{SD} =26A, V _{GS} = 0 V | | | 1.5 | V |

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